

HIGH CURRENT APPLICATION.

FEATURE

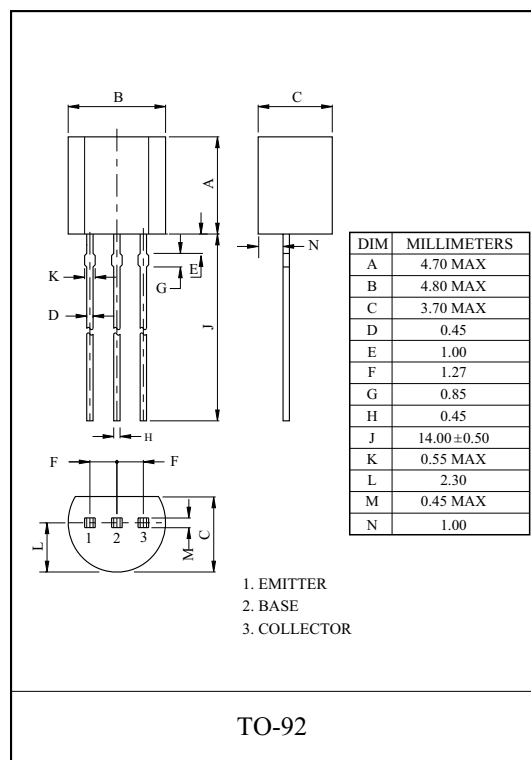
- Complementary to MPS8050.

MAXIMUM RATING (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter-Base Voltage	V_{EBO}	-6	V
Collector Current	I_C	-1.5	A
Collector Power Dissipation	P_C^*	625	mW
		400	
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55 150	°C

*Cu Lead-Frame : 625mW

Fe Lead-Frame : 400mW



ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -35V, I_E = 0$	-	-	-100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -6V, I_C = 0$	-	-	-100	nA
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -100 \mu A, I_E = 0$	-40	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -2mA, I_B = 0$	-25	-	-	V
DC Current Gain	$h_{FE(1)}$	$V_{CE} = -1V, I_C = -5mA$	45	170	-	
	$h_{FE(2)} \text{ (Note)}$	$V_{CE} = -1V, I_C = -100mA$	85	160	300	
	$h_{FE(3)}$	$V_{CE} = -1V, I_C = -800mA$	40	80	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -800mA, I_B = -80mA$	-	-0.28	-0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -800mA, I_B = -80mA$	-	-0.98	-1.2	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = -1V, I_C = -10mA$	-	-0.66	-1.0	V
Transition Frequency	f_T	$V_{CE} = -10V, I_C = -50mA$	100	200	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, f = 1MHz, I_E = 0$	-	15	-	pF

Note : $h_{FE(2)}$ Classification B:85 160 , C:120 200 , D:160 300

